Pb Free Plating Product

D10SC6MR

10 Ampere,60 Volt Dual Common Anode Schottky Barrier Half Bridge Rectifier

Features

- ✶ Low forward voltage drop
- ✶ High current capability
- ✶ Low reverse leakage current
- ✶ High surge current capability

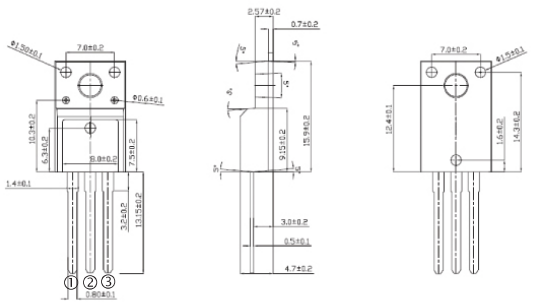
Application

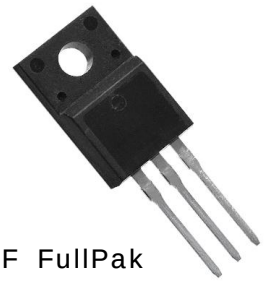
- ✶ Switching power supply
- ✶ DC/DC converter
- ✶ Home Appliances, Office Equipment
- ✶ Telecommunication

Mechanical Data

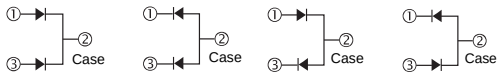
- ✶ Case: Fully Isolated Molding TO-220F
- ✶ Epoxy: UL 94V-0 rate flame retardant
- ✶ Terminals: Solderable per MIL-STD-202 method 208
- ✶ Polarity: As marked on diode body
- ✶ Mounting position: Any
- ✶ Weight: 2.1 gram approximately

ITO-220AB Unit:mm





TO-220F FullPak



Positive Common Cathode Suffix "M" | Negative Common Anode Suffix "MR" | Doubler Tandem Polarity Suffix "MD" | Reverse Doubler Tandem Polarity Suffix "MS"

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.
Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

●Absolute Maximum Ratings (If not specified Tc=25°C)

Item	Symbol	Conditions	Ratings	Unit
Storage Temperature	Tstg		-40～150	°C
Operating Junction Temperature	Tj		150	°C
Maximum Reverse Voltage	V_{RM}		60	V
Repetitive Peak Surge Reverse Voltage	V_{RRSM}	Pulse width 0.5ms, duty 1/40	65	V
Average Rectified Forward Current	Io	50Hz sine wave, R-load, Rating for each diode Io/2, Tc=120°C	10	A
Peak Surge Forward Current	I_{FSM}	50Hz sine wave, Non-repetitive 1 cycle peak value, Tj=125°C	100	A
Repetitive Peak Surge Reverse Power	P_{RRSM}	Pulse width 10 μs, Rating of per diode, Tj= 25°C	330	W
Dielectric Strength	Vdis	Terminals to case, AC 1 minute	1.5	kV
Mounting Torque	TOR	(Recommended torque 0.3N·m)	0.5	N·m

●Electrical Characteristics Tc=25°C

Item	Symbol	Conditions	Ratings	Unit
Forward Voltage	V_F	I_F=5A, Pulse measurement, Rating of per diode	Max.0.58	V
Reverse Current	I_R	V_R=V_{RM}, Pulse measurement, Rating of per diode	Max.4.5	mA
Junction Capacitance	Cj	f=1MHz, V_R=10V, Rating of per diode	Typ.200	pF
Thermal Resistance	θ jc	junction to case	Max.3.3	°C/W
	θ cf	case to heatsink, Mounting torque=0.5N·m	Max.1.5	

